

# Thyristor \ Diode Module

$$V_{RRM} = 2 \times 1800 \text{ V}$$

$$I_{TAV} = 181 \text{ A}$$

$$V_T = 1.03 \text{ V}$$

Phase leg

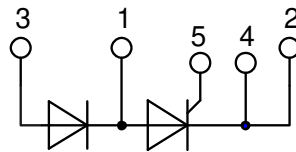
Part number

**MCD162-18io1**



Backside: isolated

 E72873



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1800	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1800 V$	$T_{VJ} = 25^{\circ}C$		300	$\mu A$
		$V_{R/D} = 1800 V$	$T_{VJ} = 125^{\circ}C$		10	mA
$V_T$	forward voltage drop	$I_T = 150 A$	$T_{VJ} = 25^{\circ}C$		1.09	V
		$I_T = 300 A$			1.25	V
		$I_T = 150 A$	$T_{VJ} = 125^{\circ}C$		1.03	V
		$I_T = 300 A$			1.25	V
$I_{TAV}$	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$		181	A
$I_{T(RMS)}$	RMS forward current	180° sine			300	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.88	V
$r_T$	slope resistance				1.15	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				0.155	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.07		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		645	W
$I_{TSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		6.00	kA
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		6.48	kA
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 125^{\circ}C$		5.10	kA
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		5.51	kA
$I^2t$	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		180.0	kA <sup>2</sup> s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		174.7	kA <sup>2</sup> s
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 125^{\circ}C$		130.1	kA <sup>2</sup> s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		126.3	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400 V \quad f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		273	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		120	W
		$t_p = 500 \mu s$			60	W
$P_{GAV}$	average gate power dissipation				8	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50 Hz$	repetitive, $I_T = 540 A$		150	A/ $\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.5 A/\mu s;$	non-repet., $I_T = 180 A$		500	A/ $\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		1000	V/ $\mu s$
		$R_{GK} = \infty; method 1 (linear voltage rise)$				
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2.5	V
			$T_{VJ} = -40^{\circ}C$		2.6	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.2	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		300	mA
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$				
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu s$
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V; I_T = 300 A; V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 100^{\circ}C$		150	$\mu s$
		$di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$				



Package Y4				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			300	A	
$T_{VJ}$	virtual junction temperature		-40		125	°C	
$T_{op}$	operation temperature		-40		100	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>					150	g	
$M_D$	mounting torque		2.25		2.75	Nm	
$M_T$	terminal torque		4.5		5.5	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	14.0	10.0		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
$V_{ISOL}$	isolation voltage	t = 1 second			3600	V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000	V	



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD162-18io1	MCD162-18io1	Box	6	454508

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 125^{\circ}\text{C}$



**Thyristor**

$V_{0\ max}$	threshold voltage	0.88	V
$R_{0\ max}$	slope resistance *	0.8	mΩ



**Outlines Y4**



Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
f	28.6	29.2	1.126	1.150
g	7.3	7.7	0.287	0.303
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
j	4.8	5.2	0.189	0.205
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	
r	1.8	2.4	0.071	0.041

Optional accessories for modules  
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



**Thyristor**



Fig. 1 Surge overload current  $I_{TSM}$ ,  $I_{FSM}$ : Crest value, t: duration



Fig. 2  $I^2dt$  versus time (1-10 ms)

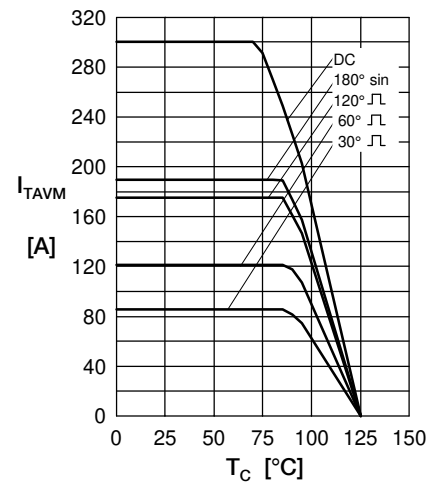


Fig. 3 Max. forward current at case temperature



Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)



Fig. 5 Gate trigger characteristics

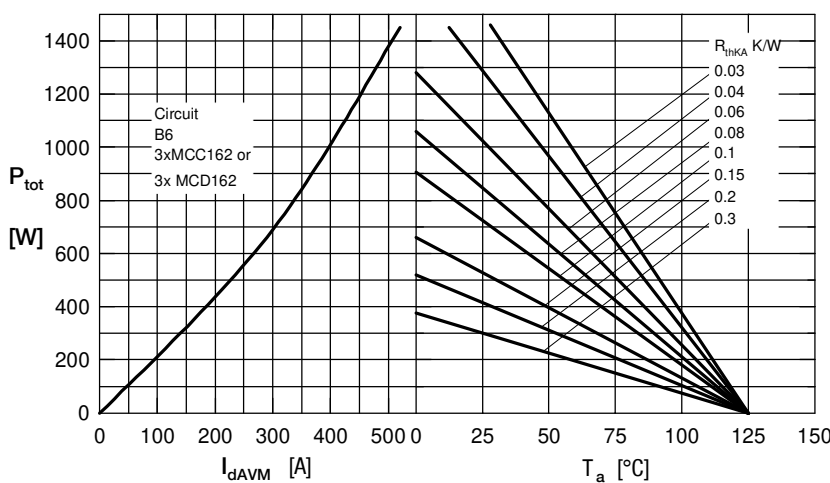


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature



Fig. 7 Gate trigger delay time



**Rectifier**

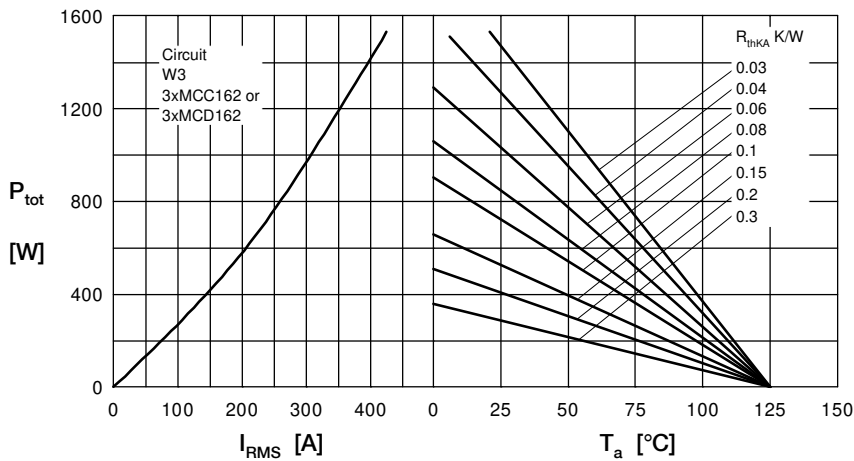
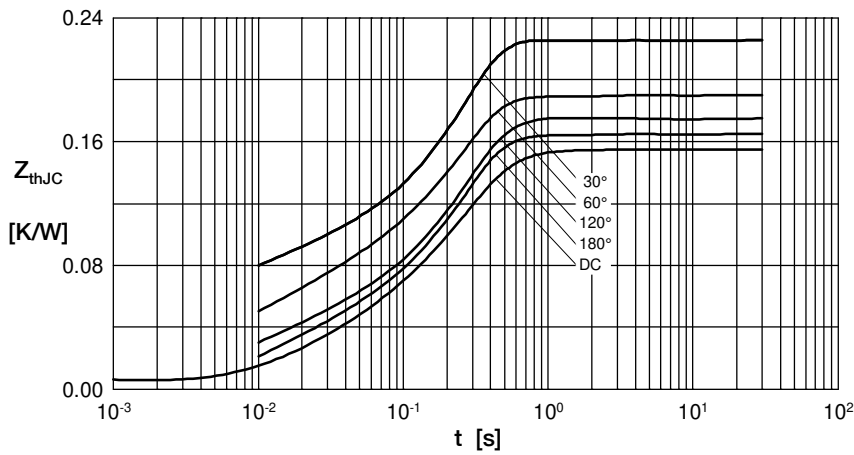


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature



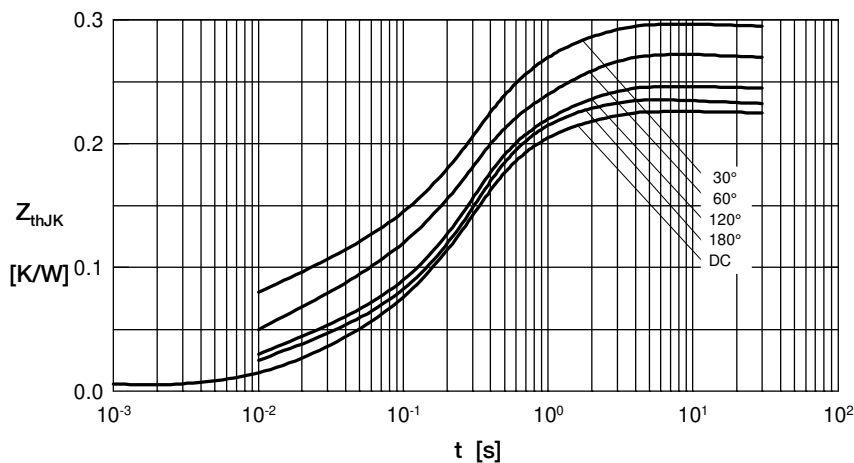
$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ [K/W]
DC	0.155
180°	0.167
120°	0.176
60°	0.197
30°	0.227

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0072	0.001
2	0.0188	0.080
3	0.1290	0.200

Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)



$R_{thJK}$  for various conduction angles d:

d	$R_{thJK}$ [K/W]
DC	0.225
180°	0.237
120°	0.246
60°	0.267
30°	0.297

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0072	0.001
2	0.0188	0.080
3	0.1290	0.200
4	0.0700	1.000

Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

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